

TDS:EMIC

拓 電 半 導 體

自主封測 品質把控 售後保障

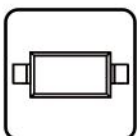
WEB | WWW.TDSEMIC.COM



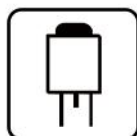
電源管理



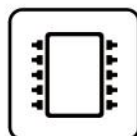
顯示驅動



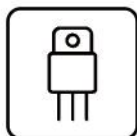
二三極管



LDO穩壓器



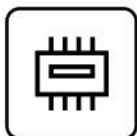
觸摸芯片



MOS管



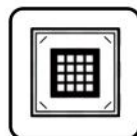
運算放大器



存儲芯片



MCU



串口通信

GBU810-TD

產品規格說明書

Reverse Voltage - 50 to 1000 Volts Forward Current - 8.0Amperes GLASS PASSIVATED BRIDGE RECTIFIERS

Features

- ◆ Surge overload rating -200 amperes peak
- ◆ Ideal for printed circuit board
- ◆ Reliable low cost construction utilizing molded plastic technique
- ◆ Plastic material has U/L lammability classification 94V-0

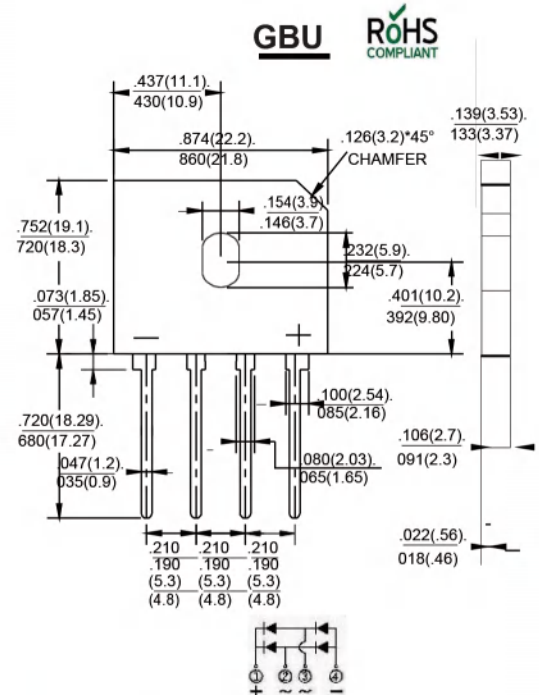
Mechanical Data

Case : JEDEC GBU Molded plastic body

Terminals : Solder plated, solderable per MIL-STD-750,Method 2026

Polarity : Polarity symbol marking on body

Mounting Position : Any



Maximum Ratings And Electrical Characteristics

Dimensions in inches and (millimeters)

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	SYMBOLS	CRK GBU8005	CRK GBU801	CRK GBU802	CRK GBU804	CRK GBU806	CRK GBU808	CRK GBU810	UNITS
Marking Code									
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward (with heatsink NOTE 2) Rectified current @ $T_c=100^\circ\text{C}$ (without heatsink)	$I_{(AV)}$				.02 9				A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}				200				A
Rating for Fusing ($t < 8.3\text{ms}$)	I^2t				166				A ² s
Maximum forward voltage at 4.0A DC	V_F				1.0				V
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=125^\circ\text{C}$	I_R				10 0.5				μA mA
Typical Junction Capacitance (Note 1)	C_J				60				pF
Typical Thermal Resistance (Note 2)	$R_{\theta JA}$				2.2				$^\circ\text{C/W}$
Operating junction temperature range	T_J				-55 to +150				$^\circ\text{C}$
storage temperature range	T_{STG}				55 to +150				C

NOTES: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2. Device mounted on 75mm*75mm*1.6mm cu plate heatsink.3

.The typical data above is for reference only.

Reverse Voltage - 50 to 1000 Volts Forward Current - 8.0Amperes

FIG.1-FORWARD CURRENT DERATING CURVE

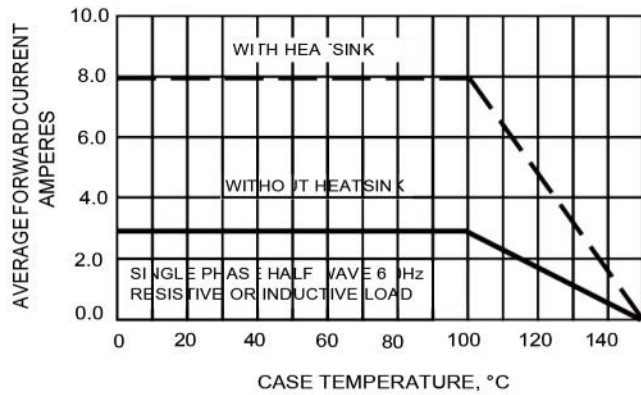


FIG.2-MAXIMUM NON-REPETITIVE SURGE CURRENT

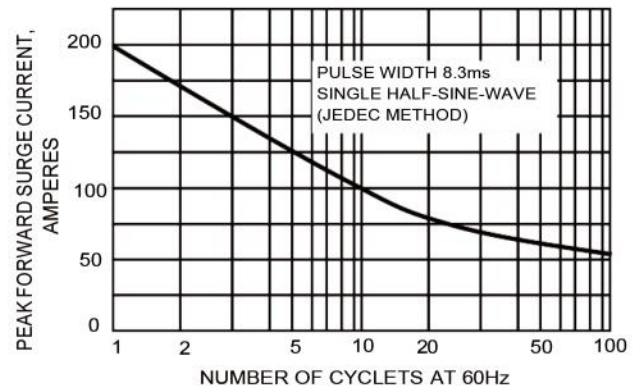


FIG.3-TYPICAL JUNCTION CAPACITANCE

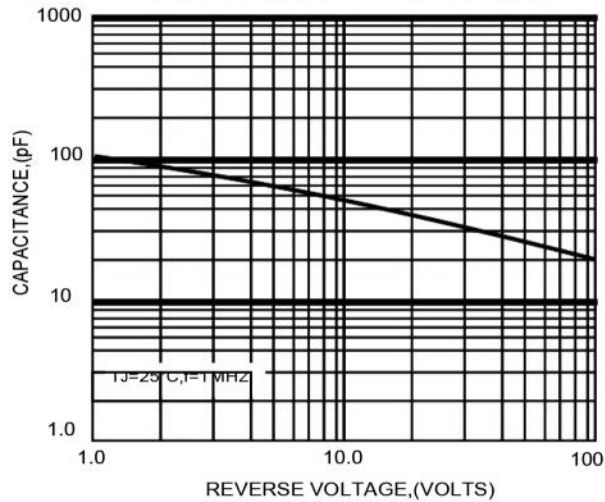


FIG.4-TYPICAL FORWARD CHARACTERISTICS

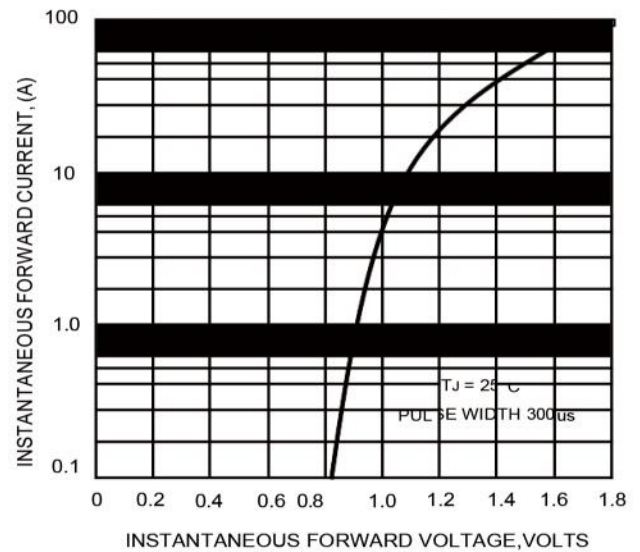


FIG.5-TYPICAL REVERSE CHARACTERISTICS

